FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON.262A	APPLICATION NO. 10/684,967
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	APPLICANT Drewes et al.	
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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
PD	1	3,623,032	11/23/71	Schapira			
	2	3,623,035	11/23/71	Kobayashi et al.			
	3	3,816,909	6/18/74	Maeda et al.			
	4	3,947,831	3/30/76	Kobayashi et al.			
	5	4,044,330	8/30/77	Johnson et al.			
	6	4,060,794	11/29/77	Feldman et al.			
	7	4,158,891	6/19/79	Fisher			
	8	4,455,626	6/19/84	Lutes			
	9	4,731,757	3/15/88	Daughton et al.			
	10	4,780,848	10/25/88	Daughton et al.			
	11	4,801,883	1/31/89	Muller et al.			
	12	4,849,695	7/18/89	Muller et al.			
	13	4,945,397	7/31/90	Schuetz			
	14	5,039,655	8/13/91	Pisharody			
	15	5,064,499	11/12/91	Fryer			
	16	5,140,549	8/18/92	Fryer			
	17	5,496,759	3/5/96	Yue et al.			
	18	5,547,599	8/20/96	Wolfrey et al.			
	19	5,569,617	10/29/96	Yeh et al.			
	20	5,587,943	12/24/96	Torok et al.			
	21	5,650,958	7/22/97	Gallagher et al.			
	22	5,701,222	12/23/97	Gill et al.			
	23	5,726,498	3/10/98	Licata et al.			
	24	5,741,435	4/21/98	Beetz, Jr. et al.			
	25	5,756,366	5/26/98	Berg et al.			
	26	5,795,823	8/18/98	Avanzino et al.			
PD	27	5,861,328	1/19/99	Tehrani et al.			

EXAMINER	DATE CONSIDERED 11/10/05

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PGP	28	5,926,394	7/20/99	Nguyen et al.			
	29	5,956,267	9/21/99	Hurst et al.			
	30	5,982,658	11/9/99	Berg et al.			
	31	6,028,786	2/22/00	Nishimura			
	32	6,048,739	4/11/00	Hurst et al.			
	33	6,136,705	10/24/00	Blair			
	34	6,153,443	11/28/00	Durlam et al.			
	35	6,174,737	1/16/01	Durlam et al.			
	36	6,218,302	4/17/01	Braeckelmann et al.			
	37	6,338,899	1/15/02	Fukuzawa et al.			
	38	6,358,756	3/19/02	Sandhu et al.			
	39	6,379,978	4/30/02	Goebel et al.			
	40	6,391,658	5/21/02	Gates et al.			
	41	6,392,922 B1	5/21/02	Liu et al.			
PGP	42	6,440,753	8/27/02	Ning et al.			
PGP	43	US 2002/0041514 A1	4/11/02	Scheler et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
PGP	44	DE 198 36 567 A1	2/24/00	Germany				X
PGP	45	EP 0 776 011 A2	5/28/97	EPO			N/A	
PGP	46	JP 2000-30222	1/28/00	Japan				X
PGP	47	WO 98/20496	5/14/98	PCT			N/A	
PGP	48	WO 00/19440	4/6/00	PCT			Abstract	

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EXAMINER INITIAL		OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
RSP	49	Chen et al., "Magnetic tunnel junction pattern technique," Journal of Applied Physics, Vol. 93, No. 10, May 15, 2003, pp. 8379-8381.
RSP	50	Kula et al., "Development and process control of magnetic tunnel junctions for magnetic random access memory devices," Journal of Applied Physics, Vol. 93, No. 10, May 15, 2003, pp. 8373-8375.
RSP	51	Pohm et al., "Experimental and Analytical Properties of 0.2 Micron Wide, Multi-Layer, GMR, Memory Elements," IEEE Transactions on Magnetics, Vol. 32, No. 5, September 1996, pp. 4645-4647.
RSP	52	Pohm et al., "The Architecture of a High Performance Mass Store with GMR Memory Cells," Nonvolatile Electronics, Honeywell Brochure, pp. 1-3.
RSP	53	Prinz, Gary A., "Magnetoelectronics," Science, Vol. 282, November 27, 1998, pp. 1660-1663.
RSP	54	Razavi et al., "Design Techniques for High-Speed, High Resolution Comparators," IEEE Journal of Solid-State Circuits, Vol. 27, No. 12, December 1992, pp. 1916-1926.
RSP	55	Wang et al., "Feasibility of Ultra-Dense Spin-Tunneling Random Access Memory," IEEE Transactions on Magnetics, Vol. 33, No. 6, November 1997, pp. 4498-4512.

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